



High density I²C EEPROM with 110 nm* technology



* F9V process

“ If only

My high-density EEPROM had an
optimized footprint, competitive pricing,
and efficient power consumption

This is where we come in

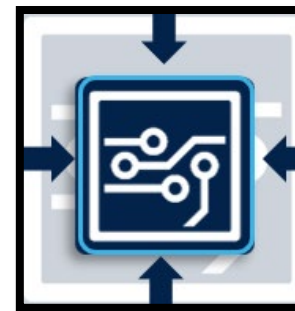


New 110 nm process addressing customer needs

ST technology roadmap 110 nm for new design

- Optimized footprint
- Competitive pricing
- Consumption effectiveness
- Wide V_{CC} range
- Plug-in replacement 150 nm

Smaller die



Consumption optimization



New features



Software Write
Protection



Custom
Device Address

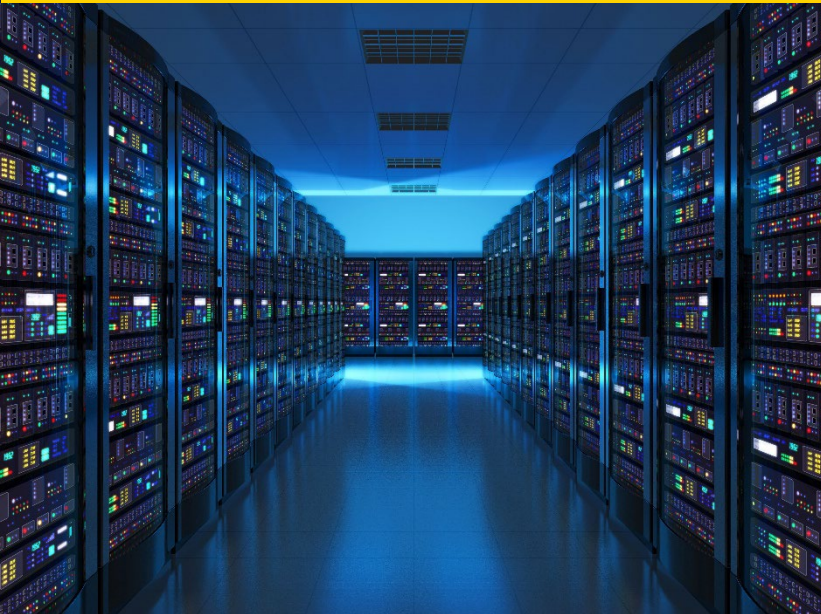
Availability





Focus application domains

Industrial



Mobile



Consumer/Healthcare



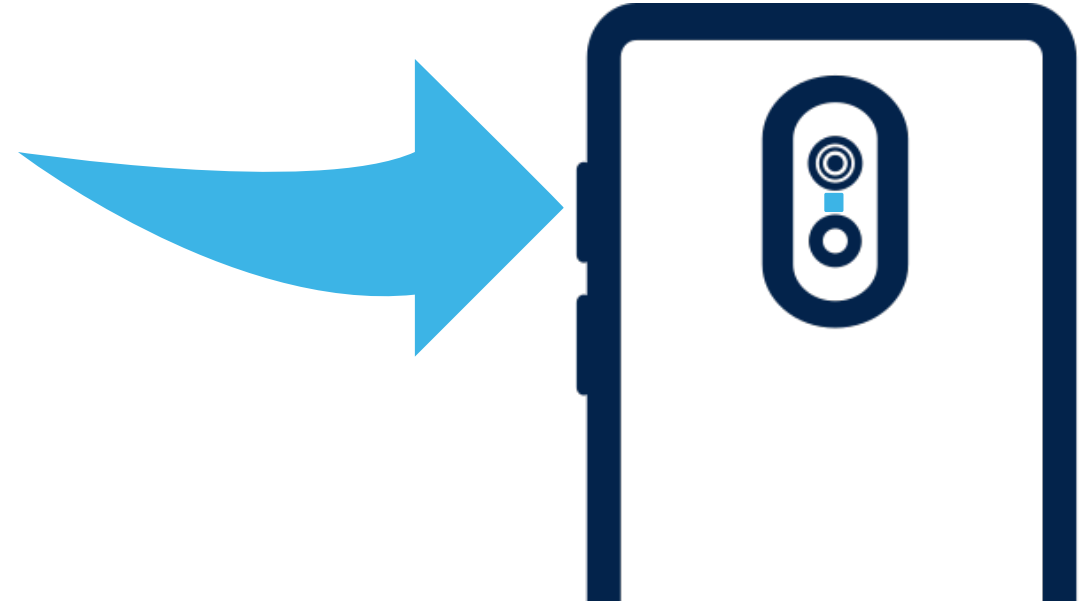
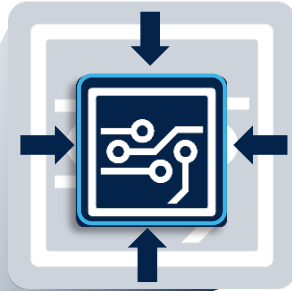


WLCSP designed for mobile

Die size reduced

Improved thickness and footprint

ST advanced
in-house
process







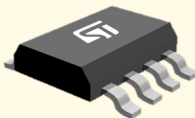






Die size divided by 2 with 110 nm vs. 150 nm



110 nm (F9V) process

I²C standard EEPROM portfolio

		PACKAGE					
		WLCSP 4-ball	WLCSP 5-ball	DFN5	DFN8	TSSOP8	SO8N
<div></div> <div>Click on product name to download the Datasheet</div>							
MEMORY DENSITY	256 Kbit (**)	M24256X-F		M24256E-F			
	512 Kbit				M24512E-F		
	1 Mbit	M24M01X-F	M24M01E-F		M24M01E-F		
	2 Mbit		M24M02E-F		M24M02E-F		
		<div>Mobile<div></div></div> <div>M24...X</div>	<div>Standard<div></div></div> <div>M24...E</div>				
		APPLICATION					

Notes:

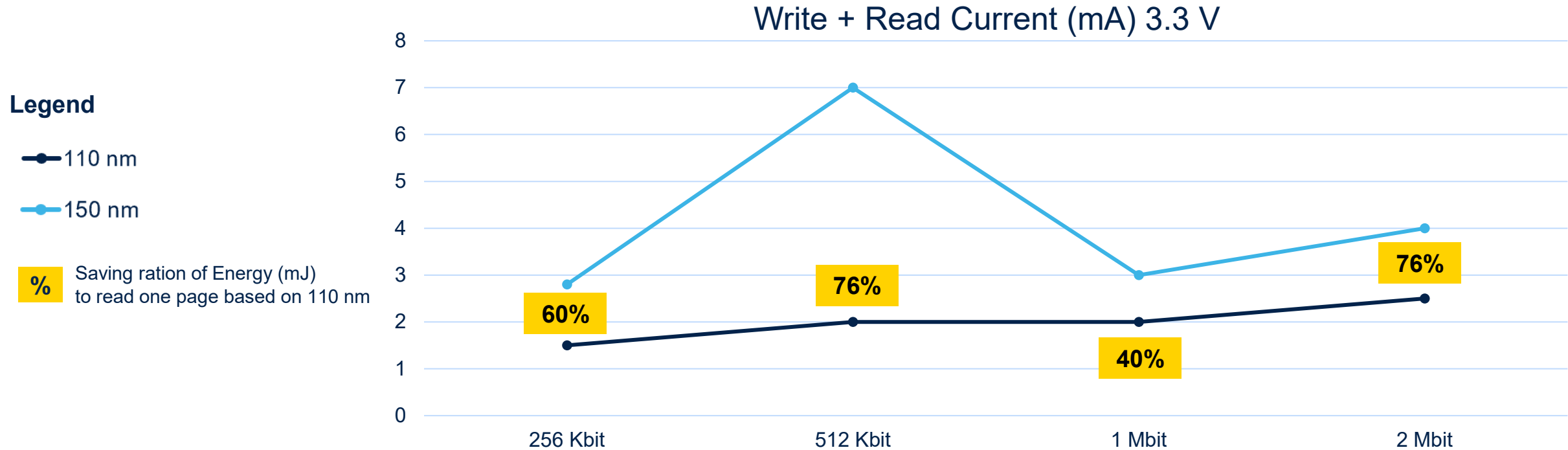
(*) - No WC (write control) in WLCSP 4-ball package

(**) - No SWP (software write protection) in DFN5, DFN8, TSSOP8, and SO8N packages for 256 Kbit memory density



Consumption 150 nm vs.110 nm

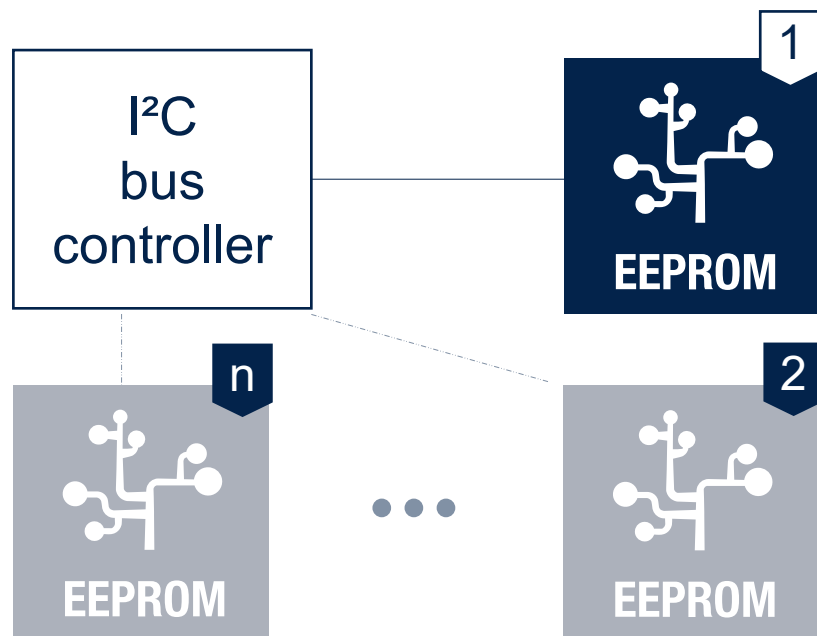
From 40 % up to 76% energy saving vs. 150 nm



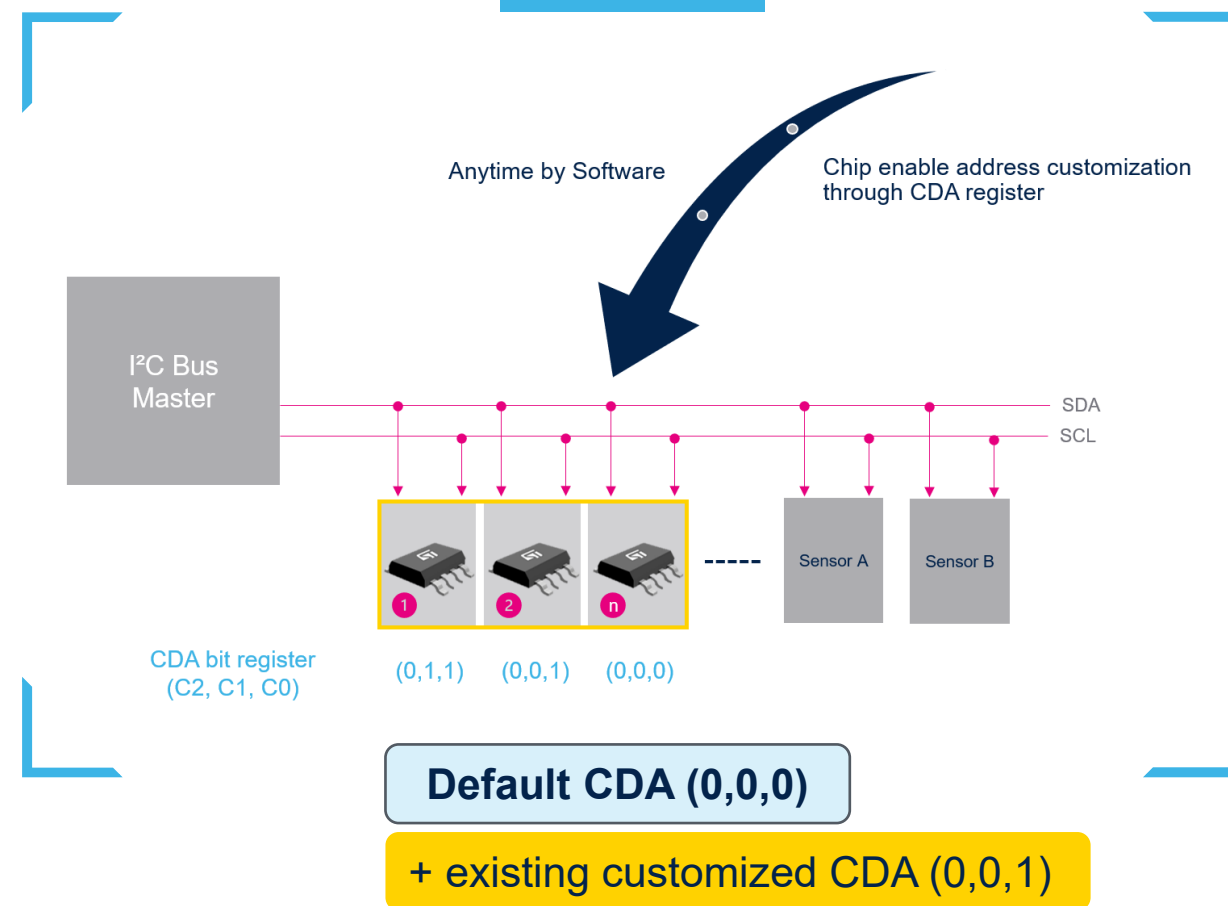


CDA register for multiple EEPROMs on same bus

Customer request



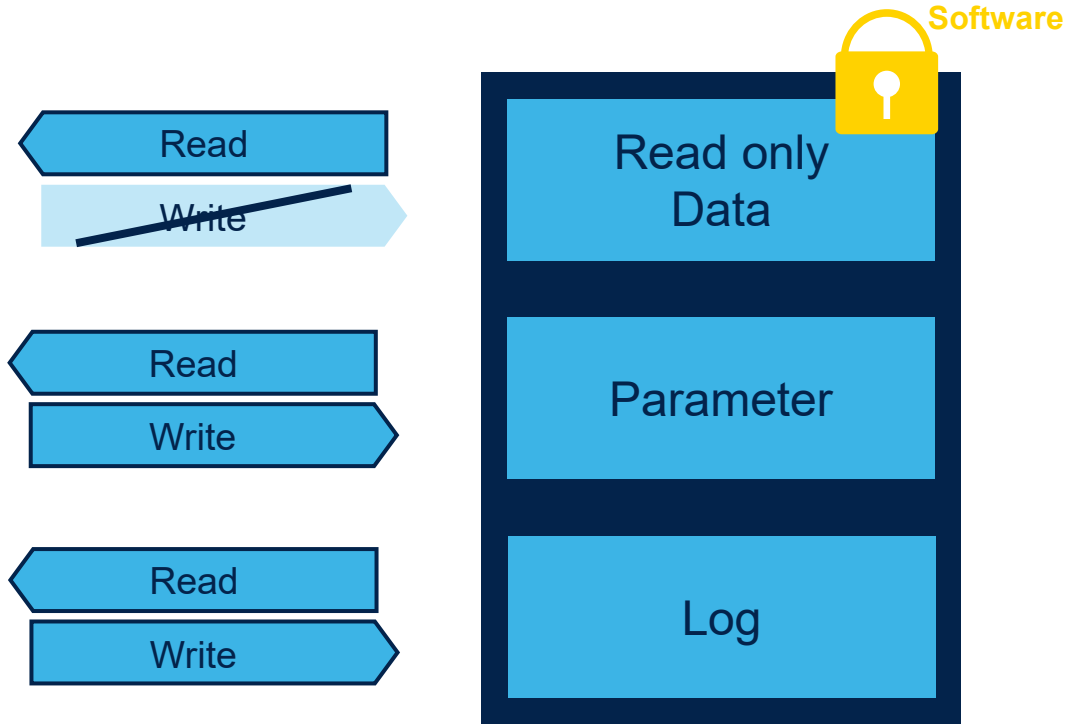
ST feature



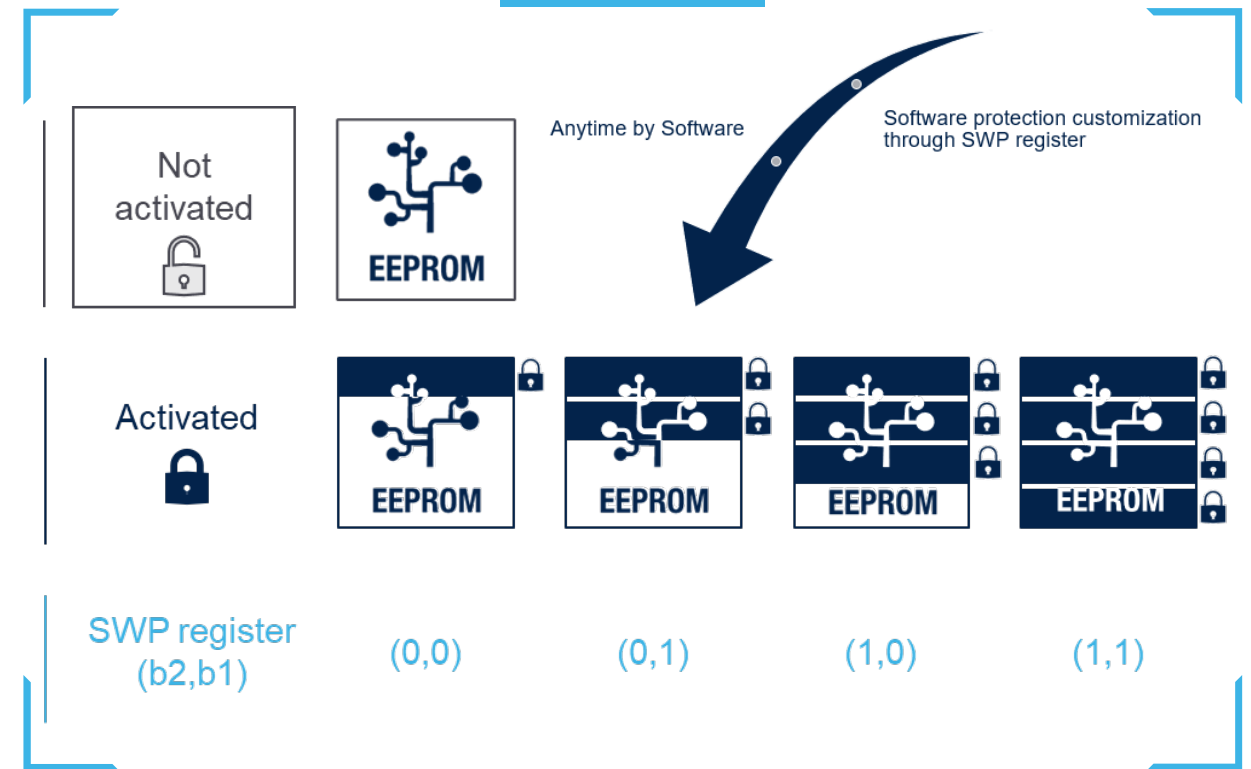


Write Protect Software for data protection

Customer request



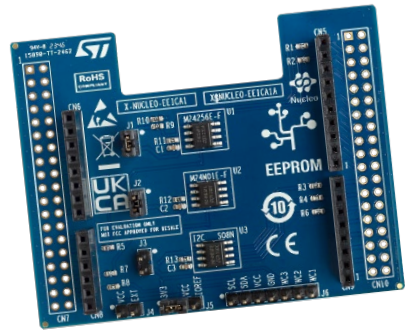
ST feature





Development tools for 110 nm EEPROM technology

STM32 Nucleo expansion board



Discover the
X-NUCLEO-EEICA1
18.23\$

STM32Cube expansion package



Get start prototyping with
X-CUBE-EEPRMA1
FREE

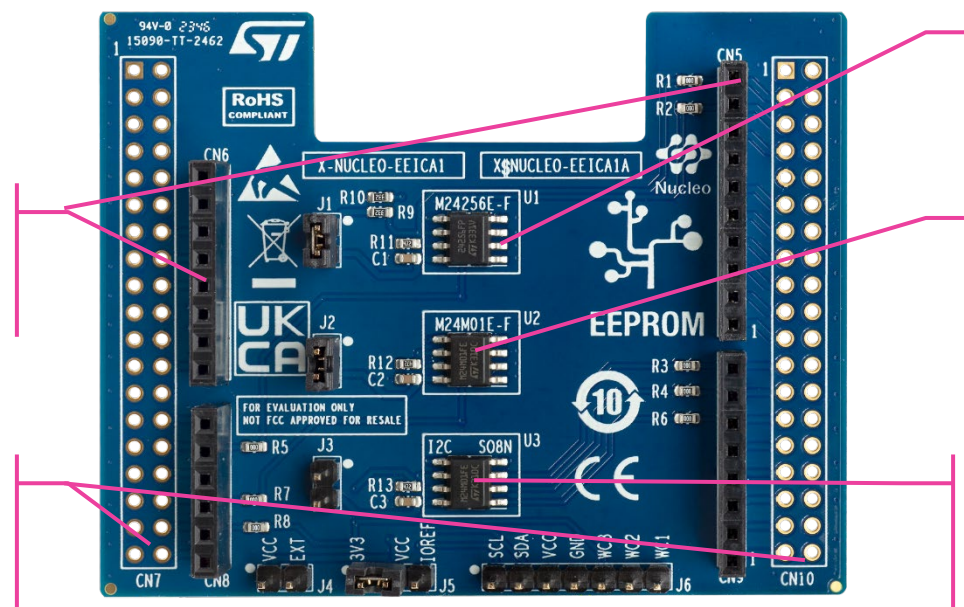
Try the new generation of EEPROM for your next design



Standard I²C EEPROM memory expansion board

Arduino Uno & ST Zio connectors:
Easy access to add-ons

ST morpho extension pins:
Direct access to all MCU I/Os



M24256E-F
Standard I²C EEPROM

M24M01E-F
Standard I²C EEPROM

External I²C EEPROM

Can be plugged on top of an STM32 NUCLEO-F401RE, NUCLEO-L053R8, NUCLEOG474RE, or NUCLEO-H743ZI development board



New high density I²C EEPROM 85°C – 110 nm

From 256-Kbit to 2-Mbit

M24256E-F, M24512E-F, M24M01E-F, M24M02E-F
High endurance (4 million write cycles), low supply (1.6 V)



- Footprint compliant with legacy EEPROM
- Long-term price competitiveness

Densities	NRND Legacy RPNs	New RPNs	Packages	New CPNs
256 Kbits	M24256-BF	M24256E-F	SO8N	M24256E-FMN6TP
	M24256-BR		TSSOP	M24256E-FDW6TP
	M24256-BW		DFN8	M24256E-FMC6TG
	M24256-DF		DFN5	M24256E-FMH6TG
	M24256-DR	M24256X-F	WLCSP4	M24256X-FCU6T/VF
512 Kbits	M24512-DF	M24512E-F	SO8N	M24512E-FMN6TP
	M24512-R		TSSOP	M24512E-FDW6TP
	M24512-W	M24512X-F*	DFN8	M24512E-FMC6TG
			WLCSP4*	M24512X-FCP6T/VF (*availability Q2-2025)
1 Mbit	M24M01-DF M24M01-R	M24M01E-F	SO8N	M24M01E-FMN6TP
			TSSOP	M24M01E-FDW6TP
		M24M01X-F	DFN8	M24M01E-FMC6TG
			WLCSP5	M24M01E-FCS6T/VF
2 Mbits	M24M02-DR	M24M02E-F	WLCSP4	M24M01X-FCU6T/VF
			SO8N	M24M02E-FMN6TP
			TSSOP	M24M02E-FDW6TP
			DFN8	M24M02E-FMC6TG
			WLCSP5	M24M02E-FCS6T/VF

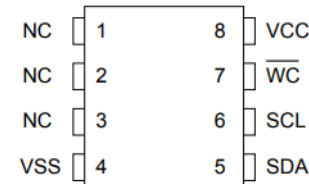
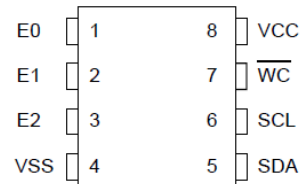
Footprint compliant ⇒ existing PCB can be reused

Dedicated CP on-demand with pre-programmed default device address ⇒ no software change



Design changes M24256-yzz vs. M24256E-F

Item	150 nm technology	110 nm technology	Why choose the 110 nm technology?
Pin package	<ul style="list-style-type: none">8 pins: SCL/SCDA/Vcc/Vss/Ei/WCEi pins for hardware chip enable address setting	<ul style="list-style-type: none">M24xxxE-F: 8-pin packageSCL/SCDA/Vcc/Vss & (WC).And 3 “Not Connected” pins (Ei pins)	<ul style="list-style-type: none">8-pin package (footprint) fully compliantEi pins: the Chip Enable Address is managed by software thru CDA*
*Configurable device address register (CDA)	The Chip Enable Address is managed by hardware through Ei pins.	The Chip Enable Address is managed by software through the CDA register.	For 110 nm products, the Chip Enable Addressing is managed by software. M24256E-FMN6TP is delivered with Chip Enable Address 0, address which can be modified later. M24256E-FMN6T4 have pre-programmed and locked Chip Enable Address “100”
Device Type Identifier	The device ‘understands’: <ul style="list-style-type: none">1010 for addressing the memory array1011 for addressing the identification page	<ul style="list-style-type: none">1010 for addressing the memory array1011 for addressing the Identification page, ID Page lock status register and CDA register.	100 nm products offer same DTI: <ul style="list-style-type: none">1010 for memory array and 1011 for Identification page (F8H)1011 for registers.The registers selection depends on MSB address values



*configurable device address register

Our technology starts with You



Find out more at [st.com/eeeprom](https://www.st.com/eeeprom)

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